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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet	2
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09/741,529

December 19, 2000

Shang, et al.

1746

**Michail Kornakov**

AMAT/5434.Y2/DISPLAY/AKT/RKK

Submission Date

April 16, 2004

[illegible]

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Number-Kind Code <sup>2</sup> (if known)				
MK	B6	JP-6033054	02/08/1994	Japan (English Abstract)		
MK	B7	DE-429809	06/04/1926	Germany		
MK	B8	WO-99/02754	01/21/1999	WIPO		

Date Considered

06/11/04

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APPLICANT

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		Number-Kind Code <sup>2</sup> (if known)				
	B1	EP-0 697 467 A1	02/21/1996	Europe		
MK	B2	JP-5-109673	04/30/1993	Japan(English Abstract)	—	
I	B3	JP-3077786	04/03/1991	Japan (English Abstract)	—	
I	B4	JP-8060368	05/03/1996	Japan (English Abstract)	—	
MK	B5	JP-6080962	03/22/1994	Japan (English Abstract)	—	

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Substitute for form 1449B/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet 3

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Application Number

09/741,529

Filing Date

December 19, 2000

First Named Inventor

Shang, et al.

Group Art Unit

1746

Examiner Name

Michail Kornakov

Attorney Docket Number

AMAT/5434.Y2/DISPLAY/AKT/RKK

Submission Date

April 16, 2004

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
MK	C1	"Seventh Generation PECVD System Announced Overcoming Obstacles to Increase the Substrate Size" AKT News Excerpt; <i>Electronic Journal</i> , Nov., 2003.	—
MK	C2	FOON, RUBY; "Kinetics of Gaseous Fluorine Reactions" <i>Prog. Reaction Kinetics</i> , 1975, Vol. 8, No. 2, pp. 81-160 Pergamon Press, Printed in Great Britain.	—
	G3	<del>European Search Report Dated October 10, 2003;</del> <del>Application No.: 01302849.3-2119</del>	—
MK	C4	Wang, X., et al, "Gas Phase Silicon Etching with Bromine Trifluoride," Transducers, 1997, Conference on Solid-State Sensors and Actuators	—

Examiner

Date Considered

06/11/2004

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PTO/SB/08A (04-03)

<b>REFERENCES FOR CONSIDERATION BY EXAMINER</b>				Application Number	09/741,529
				Filing Date	December 19, 2000
				First Named Inventor	Shang, et al.
				Group Art Unit	1746
				Examiner Name	Kornakov, M.
Sheet	1	OF	2	Attorney Docket Number	005434

### U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
		Number	Kind Code (if known)			
	A1	4,818,326		04/04/89	Liu et al.	
	A2	5,207,836		05/04/93	Chang	
	A3	5,679,215		10/21/97	Barnes et al.	
	A4	5,693,147		12/02/97	Ward et al.	
	A5	6,544,345	B1	04/08/03	Mayer et al.	

Examiner Initials	Cite No.	FOREIGN PATENT DOCUMENTS			Publication Date MM-DD-YYYY (Number 43)	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Passages or Figures Appear
		Country Code	Number	Kind Code (if known)			
	B1	WO 99/28538		A1	06/10/99	Fluoro-Gas Limited	
	B2	EP 0 819 780		A2	01/21/98	Applied Materials, Inc.	
Examiner Signature					Date Considered		

U.S. Department of Commerce, Patent and Trademark Office		Docket No.	Serial No.
(PTO Form 1449 modified)		AMAT/5434.Y2	09/741,529
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Applicant Shang, et al.	Confirmation No. 6382
(Use several sheets if necessary)		Filing Date	Group
Examiner Michael K. Karnakow		December 19, 2000	1746

**U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A1	2,879,212	03/24/1959	Hill, et al.	204	60	12/19/1955
	A2	3,146,179	08/25/1964	Davies	204	60	03/15/1962
	A3	3,684,667	08/15/1972	Sayce	204	60	07/27/1970
	A4	3,976,447	08/24/1976	Merchant, et al.	55	71	03/11/1975
	A5	4,125,443	11/14/1978	Grant, et al.	204	60	09/29/1977
	A6	4,176,018	11/27/1978	Faron	204	60	11/30/1978
	A7	4,312,718	01/26/1983	Watanabe, et al.	204	60	06/20/1980
	A8	4,498,953	02/1985	Cook, et al.	156	646	07/27/1983
	A9	4,818,326	04/04/1989	Liu, et al.	156	345	04/26/1998
	A10	4,900,395	02/13/1990	Syversen, et al.	156	639	04/07/1989
	A11	4,960,488	10/02/1990	Law, et al.	156	643	12/19/1989
	A12	5,002,632	03/26/1991	Loewenstein, et al.	156	643	11/22/1989
	A13	5,129,958	07/1992	Nagashima, et al.	134	22.1	05/23/1991

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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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	B1	51091673	08/11/1976	JP (Eng Abst)			<input checked="" type="checkbox"/>	<input type="checkbox"/>
	B2	04311570	11/04/1992	JP (Eng Abst)			<input checked="" type="checkbox"/>	<input type="checkbox"/>

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*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C1	International Sematech, "Motorola Evaluation of the Applied Science and Technology, Inc. (ASTeX) Astron Technology for Perfluorocompound (PFC) Emissions Reductions on the Applied Materials DxL Chemical Vapor Deposition (CVD) Chamber", April 16, 1999.
	C2	Astron, "Reactive Gas Generators," MKS Instruments, Inc.

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Date Considered

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Examiner Michael Kornak		December 19, 2000	1746

**U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A14	5,180,466	01/1993	Shin	156	643	04/04/1991
	A15	5,207,836	05/04/1993	Chang	134	1	06/03/1992
	A16	5,207,836	05/04/1993	Chang, Mei	134	1	06/03/1992
	A17	5,298,112	03/29/1994	Hayasaka, et al.	156	643	12/15/1992
	A18	5,336,832	08/09/1994	Keller, Alfred	585	710	11/06/1992
	A19	5,366,585	11/1994	Robertson, et al.	156	643	01/28/1993
	A20	5,378,324	01/03/1995	Hodgson	204	60	04/02/1993
	A21	5,405,491	04/11/1995	Shahvandi, et al.	156	643	03/04/1994
	A22	5,406,008	04/1995	Sievert, Allen	570	123	12/28/1989
	A23	5,425,842	06/1995	Zijlstra	438	761	06/08/1993
	A24	5,449,411	09/1995	Fukuda, et al.	118	723E	11/19/1993
	A25	5,534,107	07/1996	Gray, et al.	156	643.1	08/18/1994
	A26	5,549,802	08/27/1996	Guo, Xin S.	204	298.11	10/24/1994

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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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	B3	08017804	01/1996	JP (Eng Abst)	H01L	21/3065	<input checked="" type="checkbox"/>	<input type="checkbox"/>
	B4	0697467	02/21/1996	EP	C23C	16/44	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B5	0819780	01/21/1998	EP			<input type="checkbox"/>	<input checked="" type="checkbox"/>

**OTHER ART**

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C3	Flamm, et al., "Reaction of Fluorine Atoms with SiO <sub>2</sub> ," J. Appl. Phys., Oct. 1979 50 (10), 6211-13
	C4	Mucha, et al., "Chemiluminescent Reaction of SiF <sub>2</sub> with Fluorine and the Etching of Silicon by Atomic and Molecular Fluorine," J. Appl. Phys. 53(6) 4553-54

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*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A27	5,565,038	10/15/1996	Ashley, Ethan	134	2	05/16/1991
	A28	5,597,495	01/28/1997	Keil, et al.	216	66	11/07/1994
	A29	5,620,526	04/1997	Watatani, et al.	134	1.1	07/22/1994
	A30	5,679,215	10/21/1997	Barnes, et al.	156	646.1	01/02/1996
	A31	5,685,916	11/11/1997	Ye, et al.	134	1.1	07/07/1995
	A32	5,688,384	11/18/1997	Hodgeson, et al.	204	229	09/14/1994
	A33	5,693,147	12/02/1997	Ward, et al.	134	1.1	11/03/1995
	A34	5,705,080	01/06/1998	Leung, et al.	216	67	07/06/1994
	A35	5,756,400	05/26/1998	Ye, et al.	438	710	12/08/1995
	A36	5,762,813	06/09/1998	Takiyama, et al.	216	67	03/13/1996
	A38	5,788,799	08/04/1998	Steger, et al.	156	345	06/11/1996
	A39	5,824,607	10/1998	Trow, et al.	118	723MA	02/06/1997

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	B6	99/06611	02/11/1999	WO			<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B7	99/28538	06/19/1999	WO			<input type="checkbox"/>	<input checked="" type="checkbox"/>

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	C5	MKS ASTeX Products Announces ASTRON Ser High Flow Reactive Gas Generators for Process Chamber Cleaning Applications, from <a href="http://www.astex.com/prastrone.html">www.astex.com/prastrone.html</a> .
	C6	Donnelly, et al., "Studies of chemiluminescence accompanying fluorine atom etching of silicon: J. Appl. Phys., 51 (190) (Oct 1980) 5273-76.

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	A40	5,844,195	12/01/1998	Fairbairn, et al.	219	121.43	11/18/1996
	A41	5,846,886	12/08/1998	Hattori, et al.	438	740	02/28/1997
	A42	5,849,639	12/15/1998	Molloy, et al.	438	714	11/26/1997
	A43	5,872,061	02/16/1999	Lee, et al.	438	705	10/27/1997
	A44	5,880,031	03/09/1999	Wong	438	706	06/25/1992
	A45	5,880,032	03/09/1999	Doi, et al.	438	706	07/30/1996
	A46	5,888,309	03/30/1999	Yu	134	1.2	12/29/1997
	A47	5,904,566	05/18/1999	Tao, et al.	438	689	06/09/1997
	A48	5,935,874	08/10/1999	Kennard	438	710	03/31/1998
	A49	5,958,801	09/1999	Langley	438	738	02/20/1996
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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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	B8	0965661	12/22/1999	EP	G25B	9/00	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B9	0051938	09/08/2000	WO	C01B	7/24	<input type="checkbox"/>	<input checked="" type="checkbox"/>
	B10	00/52740	09/08/2000	WO	H01L	21/00	<input type="checkbox"/>	<input checked="" type="checkbox"/>

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	C7	Flamm, et al., "The reaction of fluorine atoms with silicon," J. Appl. Phys. 52 (5) (May 1981) 3633-39.
	C8	Flamm, et al., "XeF <sub>2</sub> and F-atom reactions with Si; their significance for plasma etching," Solid State Technology (April 1993) 117-121.

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	A52	6,007,733	12/28/1999	Jang, et al.	216	80	05/29/1998
	A53	6,020,035	02/01/2000	Gupta, et al.	427	534	10/29/1996
	A54	6,024,887	02/15/2000	Kuo, et al.	216	48	06/03/1997
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	A56	6,029,718	02/29/2000	Jackson, et al.	141	231	06/26/1998
	A57	6,051,505	04/18/2000	Chu, et al.	438	710	03/05/1998
	A58	6,109,206	08/29/2000	Mayden, et al.	118	723IR	05/29/1997
	A59	6,117,793	09/2000	Tang	438	740	09/03/1998
	A60	6,125,859	10/03/2000	Kao, et al.	134	1.1	07/11/1997
	A61	6,159,333	12/12/2000	Gupta, et al.	156	345	10/08/1998
	A62	6,255,222	07/24/2001	Herchen, et al.	216	60	06/16/2000
	A63	6,264,852	07/24/2001	Herchen, et al.	216	60	06/16/2000
	A64	6,271,148	08/07/2001	Kao, et al.	438	727	10/13/1999
	A65	6,286,451	09/2001	Ishikawa, et al.	118	723I	05/29/1997
	A66	6,352,081	03/05/2002	Lu, et al.	134	22.1	07/09/1999

**Foreign Patent Documents**

*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
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	B11	1076355	02/14/2001	EP	H01L	21/00	<input type="checkbox"/>	<input type="checkbox"/>

**OTHER ART**

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C9	Ibbotson, D.E., et al., "Comparison of XeF <sub>2</sub> and F-Atom Reactions with Si and SiO <sub>2</sub> ," March 28, 1984.
	C10	Aliev, V.S., et al., "Development of Si (100) Surface Roughness at the Initial Stage of Etching in F <sub>2</sub> and XeF <sub>2</sub> Gases; Ellipsometric Study," Surface Science, 206-14 (1999).

Examiner

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**U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A67	6,362,031	03/2002	Yamaguchi, et al.	438	158	11/24/1999
	A68	6,366,366	04/02/2002	Nakamura	358	487	08/20/1998
	A69	6,374,831	04/23/2002	Chandran, et al.	134	1.1	02/04/1999
	A70	6,379,575	04/30/2002	Yin, et al.	216	67	10/21/1997
	A71	6,387,288	05/14/2002	Bjorkman, et al.	216	67	04/21/2000
	A72	6,500,356	12/31/2002	Goto, et al.	216	72	03/27/2000
	A73	6,544,345	04/08/2003	Mayer, et al.	134	28	07/12/2000
	A74	6,602,433	08/05/2003	Bhardqaj, et al.	216	37	04/06/2000

**For Ign Patent Documents**

*Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						YES	NO

**OTHER ART**

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C11	Habuka, H, et al., "Dominant overall chemical reaction in a chlorine trifluoride-silicon-nitrogen system at atmospheric pressure," Jpn. J.Appl. Phys., (1999) 38 6466-69.
	C12	Larson, P.R., et al., "Atomic Fluorine Beam Etching of Silicon and Related Materials," J. Vac. Sci. Tech. B (1999).
	C13	Petition to Withdraw Application from Issuance and Reject the Application as Being Invalid, October 22, 2003
	C14	References for Consideration by Examiner, November 7, 2003
	C15	

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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Department of Commerce, Patent and Trademark Office		Docket No.	Serial No.
(PTO Form 1449 modified)		AMAT/5434.Y2	09/741,529
<b>SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Applicant Shang, et al.	Confirmation No. 6382
(Use several sheets if necessary)		Filing Date	Group
Examiner Michael Kornatov		December 19, 2000	1746

**U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A75	2002/0074013	06/20/2002	Yadav, et al.	134	1.1	12/19/2000
	A76	2003/0010354	01/16/2003	Goto, et al.	134	1.1	04/27/2000
	A77	2003/0109144	06/12/2003	Goto, et al.	438	734	12/24/2002
	A78	2003/0121796	06/12/2003	Goto, et al.	438	734	12/24/2002

**For Ign Patent Documents**

*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO

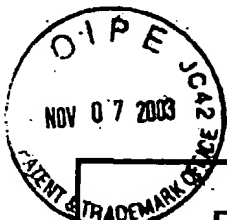
**OTHER ART**

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
	C16	
	C17	

Examiner

Date Considered

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**REFERENCES FOR  
CONSIDERATION BY EXAMINER**

Application Number	09/741,529
Filing Date	December 19, 2000
First Named Inventor	Shang, et al.
Group Art Unit	1746
Examiner Name	Kornakov, M.
Atty Docket Number	005434

Sheet 2 of 2

Examiner Initials	Cite No.	OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS	Date
	C1	International Sematech, "Motorola Evaluation of the Applied Science and Technology, Inc. (ASTeX) Astron Technology for Perfluorocompound (PFC) Emissions Reductions on the Applied Materials DxL Chemical Vapor Deposition (CVD) Chamber."	April 16, 1999
	C2	Astron, "Reactive Gas Generators," MKS Instruments, Inc., 4 pages.	
	C3	Flamm et al., "Reaction of Fluorine Atoms with SiO <sub>2</sub> ," J. Appl. Phys., 50 (10), pages 6211-3,	October 1980
	C4	Mucha et al., "Chemiluminescent Reaction of SiF <sub>2</sub> with Fluorine and the Etching of Silicon by Atomic and Molecular Fluorine," (6), Pages 4553-4, J. Appl. Phys., 53(6).	June 1982
Examiner Signature		Date Considered	